



# FINITE ELEMENT MODELING OF AN ALGAN/GAN BASED VOC SENSOR USING COMSOL

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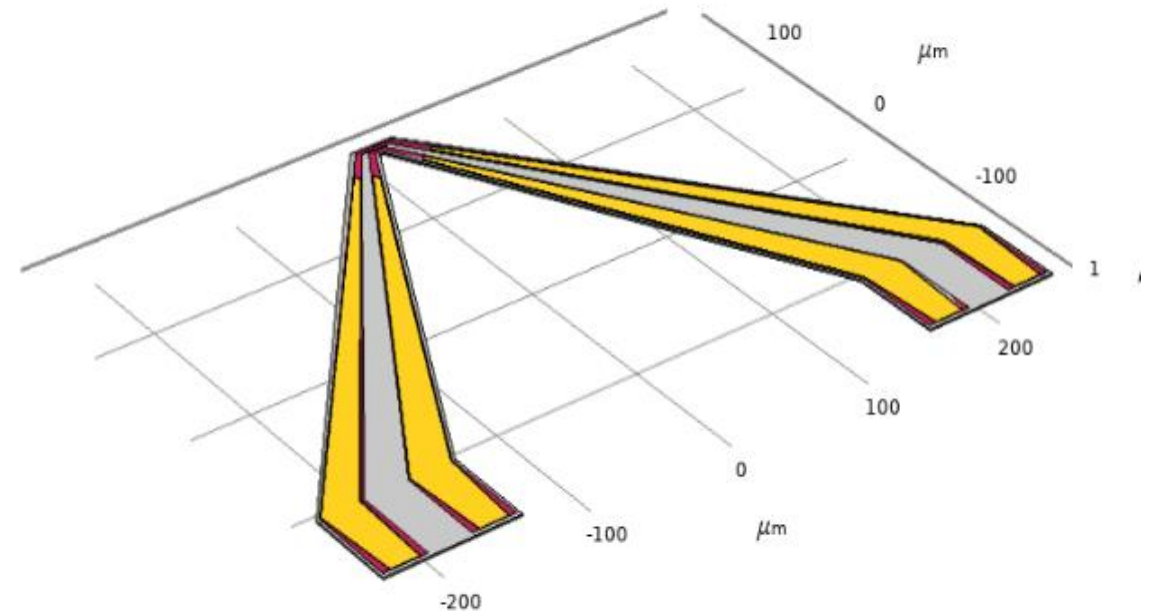
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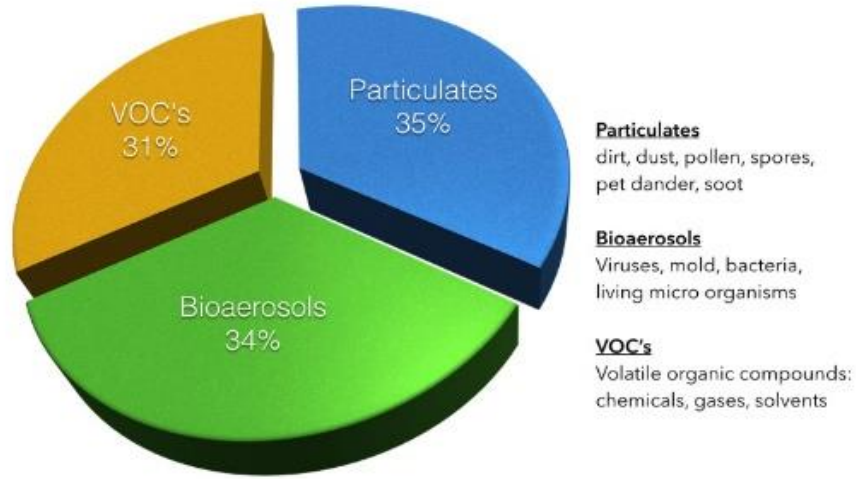
# Outline

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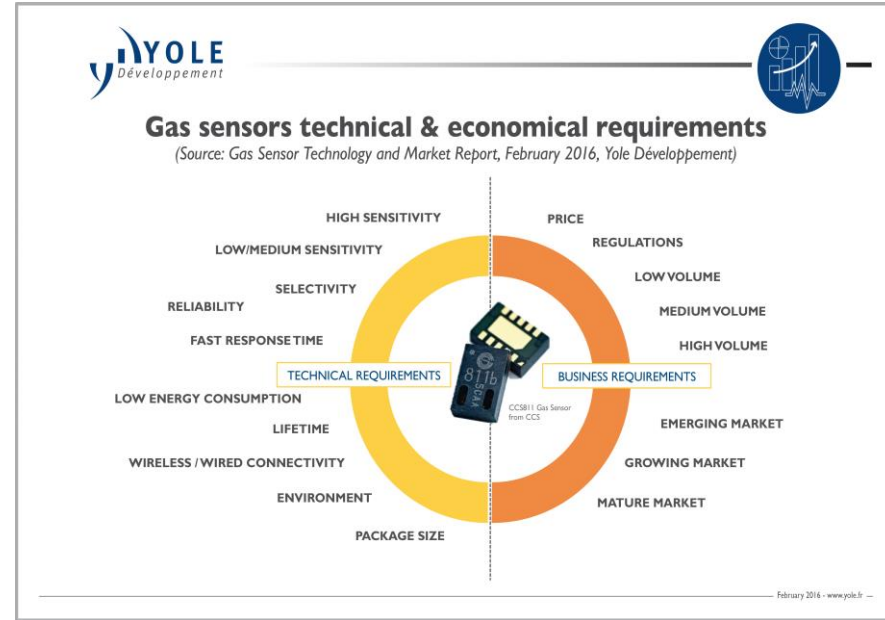




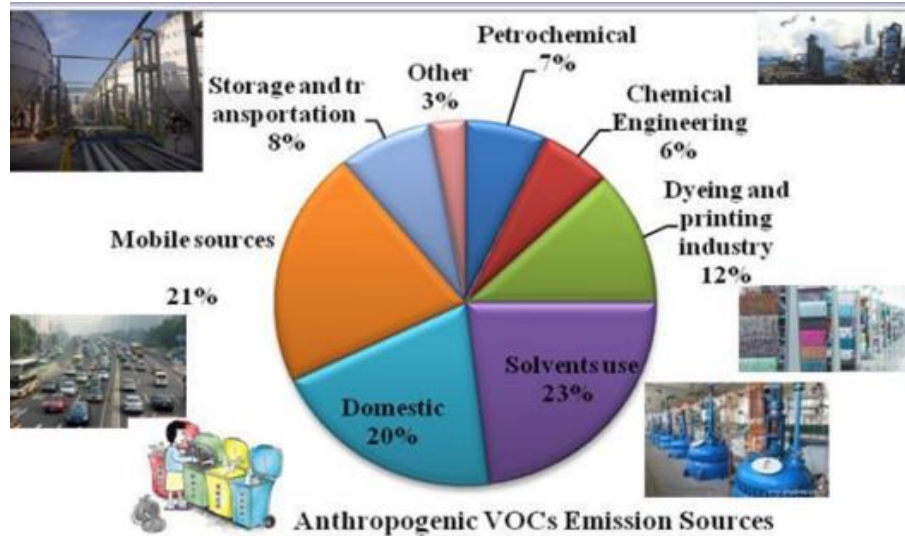
# Introduction



Source: H. Guo et al., Environ. Res. 94 (1), 57-66 (2004)



Source: Yole Développement



Source: <https://www.healthypeople.gov/2020/topics-objectives/topic/respiratory-diseases>

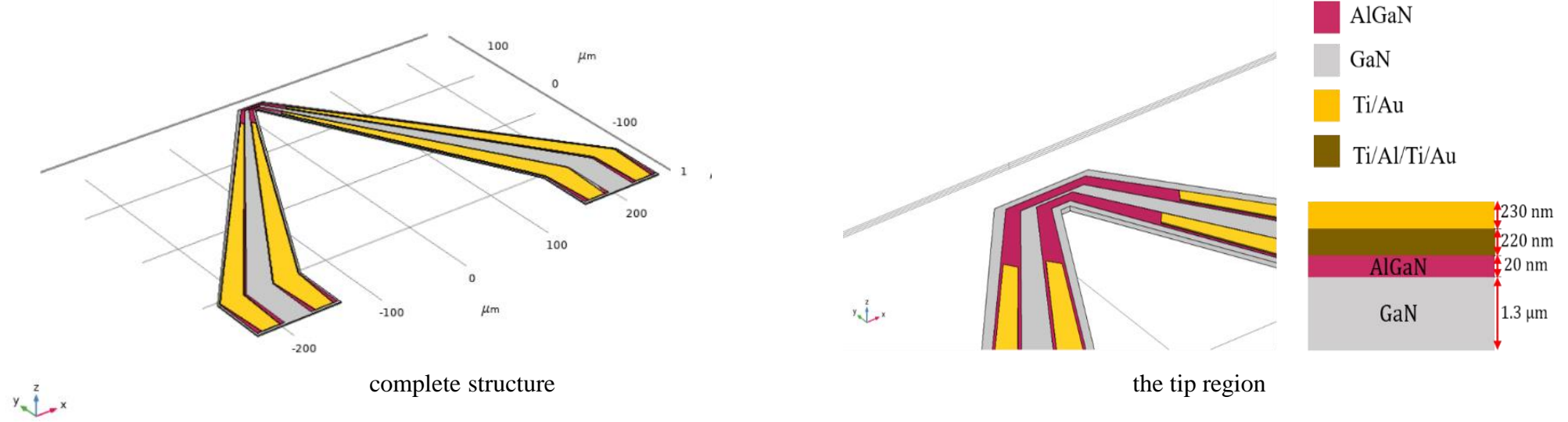
- An AlGa<sub>N</sub>-Ga<sub>N</sub>-AlGa<sub>N</sub> based dual channel microcantilever has been simulated to compute the temperature profiles
- Using the electric currents (*ec*) module, the electric field intensity, current density and the electromagnetic loss profiles of the cantilever are computed
- By coupling the *ec* module with heat transfer (*ht*) module, the temperature profiles are obtained



# Geometry Setup



3D Geometry of the AlGaN-GaN-AlGaN dual channel micro cantilever



- To compute the temperature profiles of the cantilever at different bias voltages the required material properties are
  - electrical conductivity ( $\sigma$ ),
  - relative permittivity ( $\epsilon_r$ ),
  - thermal conductivity ( $k$ ),
  - density ( $\rho$ )
  - heat capacity at constant pressure ( $c_p$ )

Table 1 illustrates the properties of all the materials used in the simulation

|                             | GaN  | AlGaN | Metal stack 1 | Metal stack 2 |
|-----------------------------|------|-------|---------------|---------------|
| $\sigma$ (S/m)              | 1695 | 96154 | 2.6e6         | 2.6e6         |
| $\epsilon_r$                | 9.5  | 8.9   | 1             | 1             |
| (W/(m.K))                   | 41   | 52.7  | 21.9          | 317           |
| $\rho$ (kg/m <sup>3</sup> ) | 6150 | 5740  | 4506          | 19300         |
| $c_p$ (J/(kg.K))            | 490  | 490   | 522           | 129           |



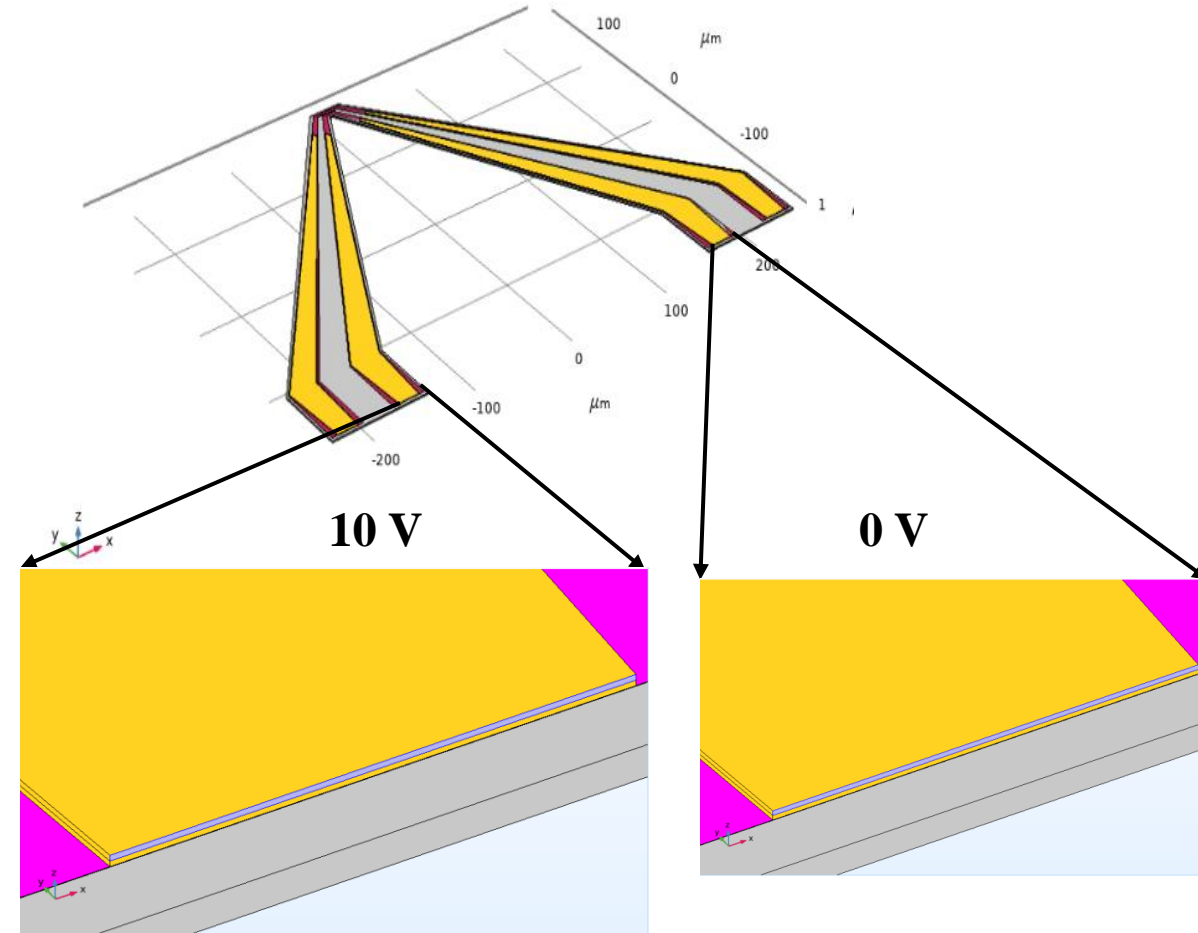


# Simulation procedure



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- For the given 3D geometry, the temperature profiles at different bias voltages are computed using the electric currents (*ec*) and heat transfer (*ht*) modules
- Using the *ec* module, electric potential boundary conditions are used to apply the bias voltages on the inner channels
  - For instance, in this simulation DC bias voltages such as 10 V and 0 V are applied on the edge boundaries of the gold layers located at the left and right arms of the cantilever base region respectively
- From the electric potential ( $V$ ), the profiles of electric field intensity ( $E$ ), current density ( $J$ ), and electromagnetic losses ( $Q_e$ ) are computed





# Simulation procedure cont....



$$E = -\nabla V, \quad (1)$$

$$J = \sigma \cdot E, \quad (2)$$

$$\nabla \cdot J = Q_e. \quad (3)$$

The electromagnetic loss data obtained from the *ec* module is given as input to the *ht* module to solve the heat equation which can be written as

$$(\rho \cdot c_p \cdot \vec{u}) \cdot \nabla T = \nabla \cdot (\vec{q}) + Q_e, \quad (4)$$

$$\text{where } \vec{q} = k \cdot \nabla T. \quad (5)$$

In Eq. (4)  $\vec{u}$  is the fluid velocity vector,  $T$  is the temperature and  $\vec{q}$  is the conductive heat flux. Convective and radiative heat losses are also considered in the simulation. The equation to represent the convective heat loss can be written as

$$-\vec{n} \cdot \vec{q} = q_0, \quad (6)$$

$$\text{where } q_0 = h \cdot (T_{ext} - T). \quad (7)$$

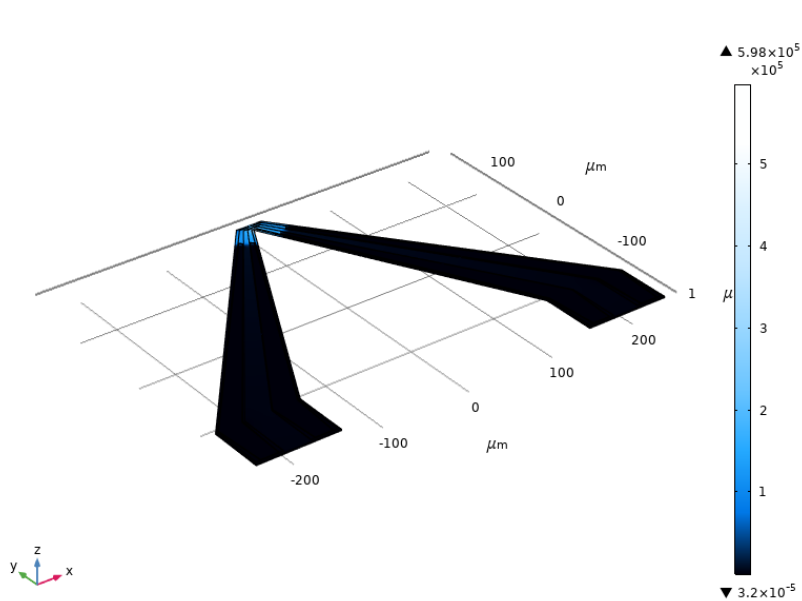
The equation to compute the radiative heat loss can be written as

$$-\vec{n} \cdot \vec{q} = \varepsilon \cdot \sigma \cdot (T_{amb}^4 - T^4), \quad (8)$$

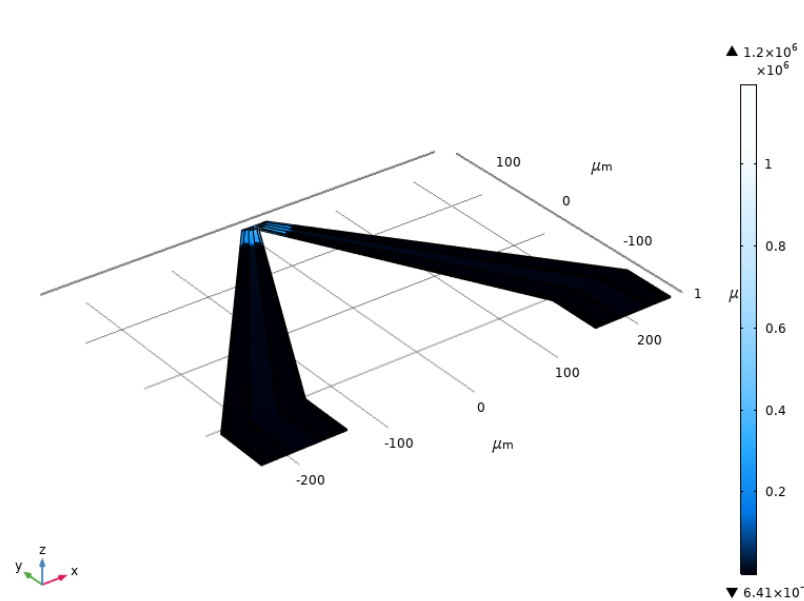




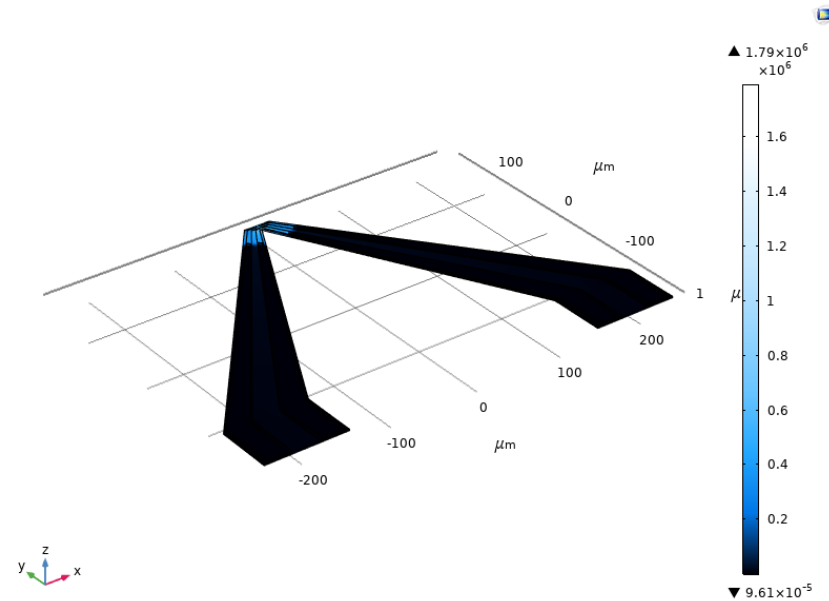
# Electric Field Intensity profile



At bias voltage of 10 Volts



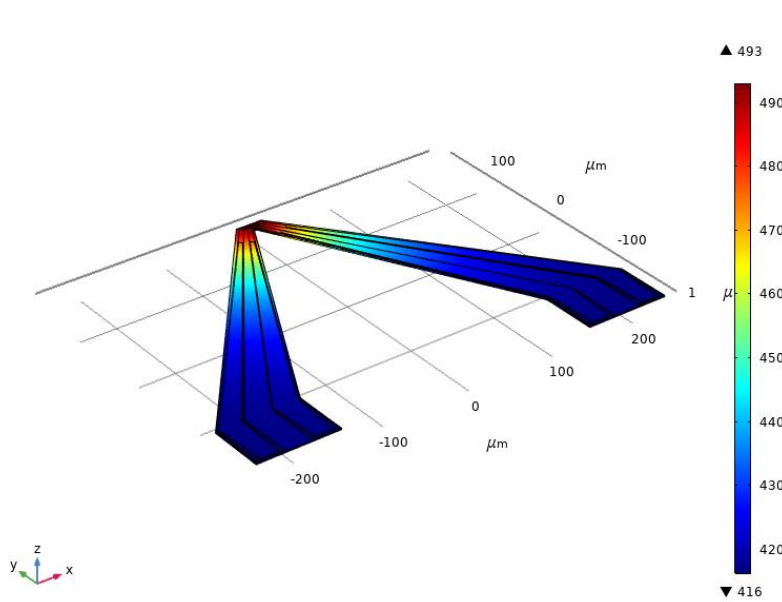
At bias voltage of 20 Volts



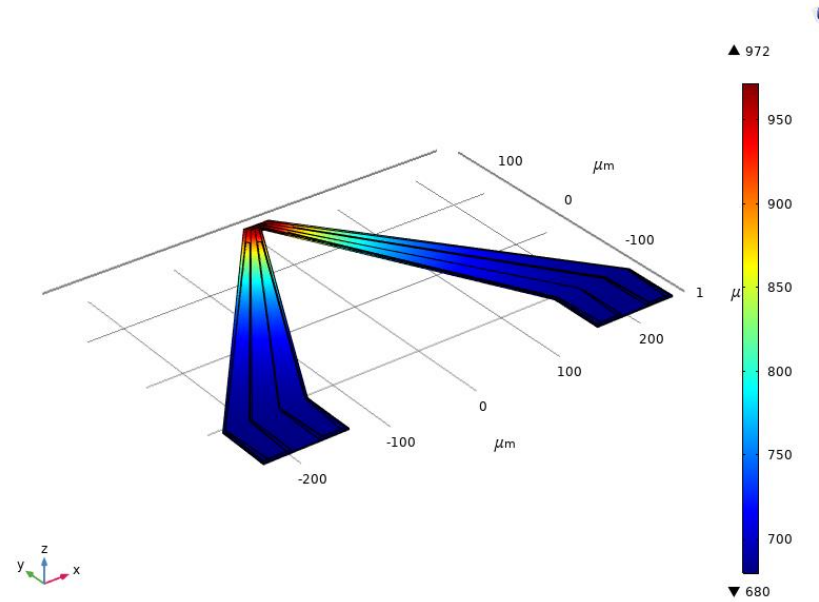
At bias voltage of 30 Volts



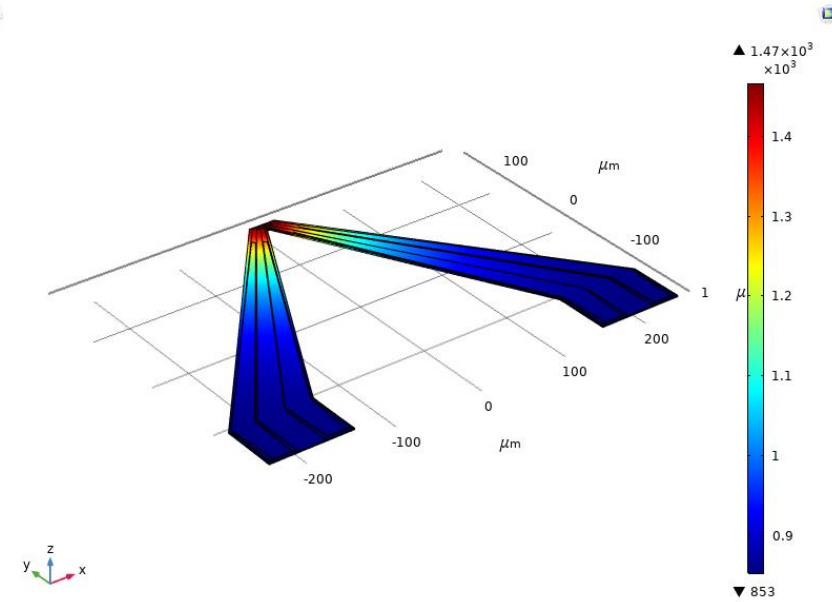
# Temperature Profile



At bias voltage of 10 Volts



At bias voltage of 20 Volts



At bias voltage of 30 Volts





# Conclusion



- An AlGa<sub>N</sub>-Ga<sub>N</sub>-AlGa<sub>N</sub> based dual channel cantilever has been simulated in COMSOL to obtain the temperature profiles at different DC bias voltages
- To perform the simulations the electric currents and heat transfer modules are coupled
- The DC bias voltages are varied from 5 V to 30 V with a step size of 5 V
- From the simulation results, it can be concluded that at every bias voltage the magnitude of electric field intensity and temperature is maximum at the tip region of the cantilever
- Also, as the applied bias voltage increases, the electric field intensity and temperature also increases
- The numerical results obtained from these simulations are useful for validating the experimental results



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